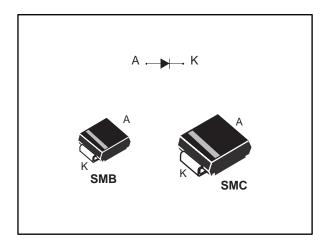
# **STTH212**



## High voltage ultrafast diode

Datasheet - production data



### **Features**

- Low forward voltage drop
- High reliability
- High surge current capability
- Soft switching for reduced EMI disturbances
- Planar technology

### **Description**

This device is an ultrafast diode based on a high voltage planar technology, it is perfectly suited for freewheeling, clamping, snubbering, demagnetization in power supplies and other power switching applications.

Housed in SMB and SMC packages, this diode reduces the losses in high switching frequency operations.

**Table 1: Device summary** 

Symbol	Value
I <sub>F(AV)</sub>	2 A
V <sub>RRM</sub>	1200 V
T <sub>j</sub>	175 °C
V <sub>F</sub> (typ.)	1.0 V
t <sub>rr</sub> (max.)	75 ns

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### 1 Characteristics

Table 2: Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit		
V <sub>RRM</sub>	Repetitive peak reverse voltage			1200	V
V <sub>(RMS)</sub>	RMS voltage			850	V
1	Average forward current $\delta$ = 0.5,	ent $\delta$ = 0.5, SMB $T_{lead}$ = 90 °C	T <sub>lead</sub> = 90 °C	2	Α
I <sub>F(AV)</sub>	square wave		T <sub>lead</sub> = 105 °C	2	A
I <sub>F(RMS)</sub>	RMS forward current	10			
IFSM	Forward surge current t <sub>p</sub> = 8.3 ms			40	A
T <sub>stg</sub>	Storage temperature range			-50 to +175	°C
Tj	Maximum operating junction temperature			175	°C

**Table 3: Thermal parameters** 

Symbol	Parameter		Maximum	Unit
D	lunction to load	SMB	25	°C/W
R <sub>th(j-l)</sub>	Junction to lead	SMC	20	C/VV

Table 4: Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
	Doverse leeke as overent	T <sub>j</sub> = 25 °C	$V_R = V_{RRM}$	-		10	μA
IR	I <sub>R</sub> Reverse leakage current	T <sub>j</sub> = 125 °C		-		100	
		T <sub>j</sub> = 25 °C		-		1.75	
VF	Forward voltage drop	T <sub>j</sub> = 125 °C	I <sub>F</sub> = 2 A	-	1.07	1.50	V
				-	1.0	•	

To evaluate the conduction losses, use the following equation:

 $P = 1.26 \text{ x } I_{F(AV)} + 0.12 \text{ x } I_{F^2(RMS)}$ 

**Table 5: Dynamic characteristics** 

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
t <sub>rr</sub>	Reverse recovery time	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = -100 A/μs; V <sub>R</sub> = 30 V	-	-	75	ns
t <sub>fr</sub>	Forward recovery time	$I_F = 2 A;$		-	-	500	
V <sub>FP</sub>	Forward recovery voltage	1j = 25 C	$dI_F/dt = 50 \text{ A/}\mu\text{s};$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$	-	-	30	V

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### 1.1 Characteristics (curves)

0.50 0.75

1.00 1.25 1.50

0.0

Figure 2: Forward voltage drop versus forward current

50 I<sub>FM</sub>(A)
45 I<sub>T,=125°C</sub> (Maximum values)
35 I<sub>T,=125°C</sub> (Maximum values)
46 I<sub>T,=125°C</sub> (Maximum values)
47 I<sub>T,=25°C</sub> (Maximum values)
48 I<sub>T,=125°C</sub> (Maximum values)
49 I<sub>T,=125°C</sub> (Maximum values)
40 I<sub>T,=125°C</sub> (Maximum values)
40 I<sub>T,=125°C</sub> (Maximum values)
41 I<sub>T,=125°C</sub> (Maximum values)

Figure 3: Relative variation of thermal impedance junction to ambient versus pulse duration (Epoxy printed circuit board FR4, Scu = 1 cm2)

1.75

2.00 2.25

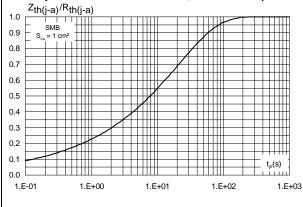


Figure 4: Relative variation of thermal impedance junction to ambient versus pulse duration (Epoxy printed circuit board FR4, S<sub>CU</sub> = 1 cm2)

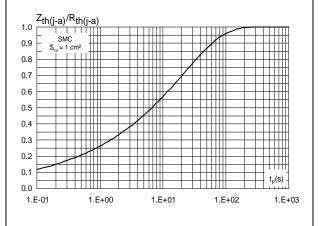


Figure 5: Reverse recovery current versus dl<sub>F</sub>/dt (typical values)

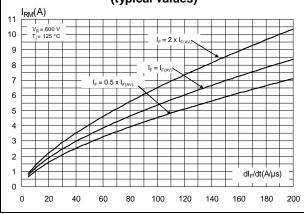
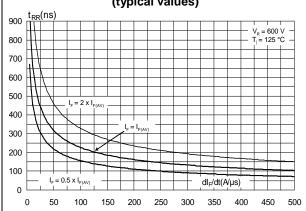


Figure 6: Reverse recovery time versus dlr/dt (typical values)





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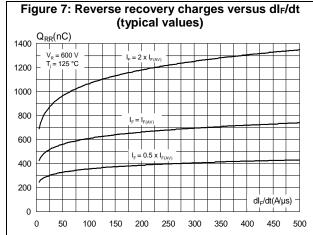
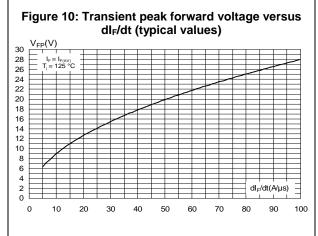
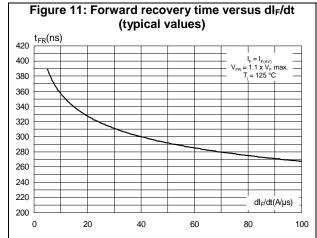
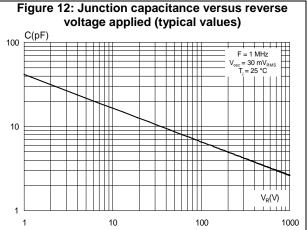


Figure 8: Softness factor versus dl<sub>F</sub>/dt (typical values) 6.0  $I_F = I_{F(AV)}$   $V_R = 600 \text{ V}$   $T_j = 125 \text{ °C}$ 5.5 5.0 4.5 4.0 3.5 3.0 2.5 2.0 1.5 1.0 0.5  $dI_F/dt(A/\mu s)$ 0.0 0 25 75 100 125 200 225

Figure 9: Relative variations of dynamic parameters versus junction temperature 0.9 0.8 0.7 0.6 0.5 0.4 0.3 0.2  $I_F = I_{F(AV)}$   $V_R = 600 \text{ V}$ Reference:  $T_j = 125 \text{ °C}$ 0.1 T<sub>i</sub>(°C) 0.0 50 75 100 125 25

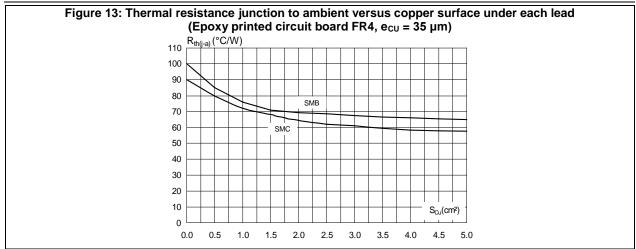






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Package information STTH212

#### 2 **Package information**

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Epoxy meets UL94, V0

#### **SMB** package information 2.1

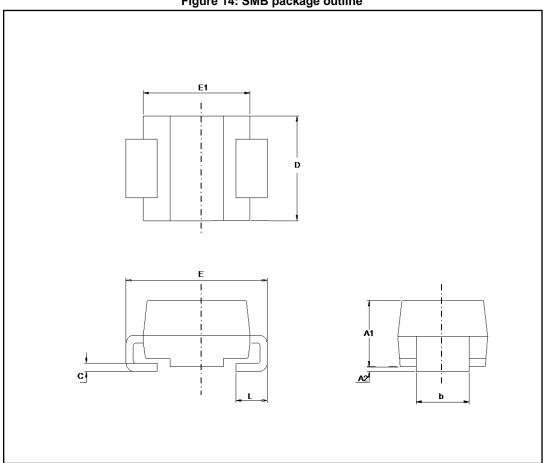


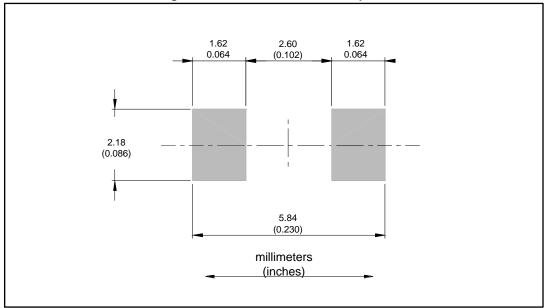
Figure 14: SMB package outline

STTH212 Package information

Table 6: SMB package mechanical data

	Dimensions			
Ref.	Millin	neters	Inc	hes
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.0748	0.0965
A2	0.05	0.20	0.0020	0.0079
b	1.95	2.20	0.0768	0.0867
С	0.15	0.40	0.0059	0.0157
D	3.30	3.95	0.1299	0.1556
Е	5.10	5.60	0.2008	0.2205
E1	4.05	4.60	0.1594	0.1811
L	0.75	1.50	0.0295	0.0591

Figure 15: SMB recommended footprint



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# 2.2 SMC package information

Figure 16: SMC package outline

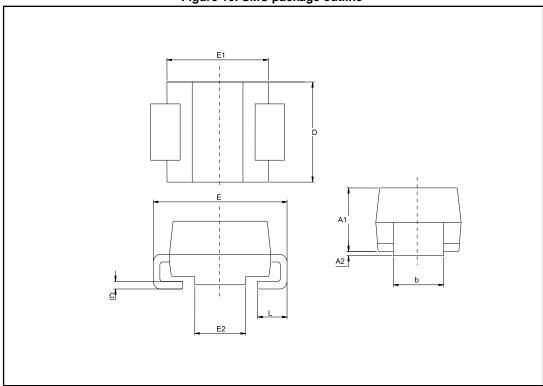
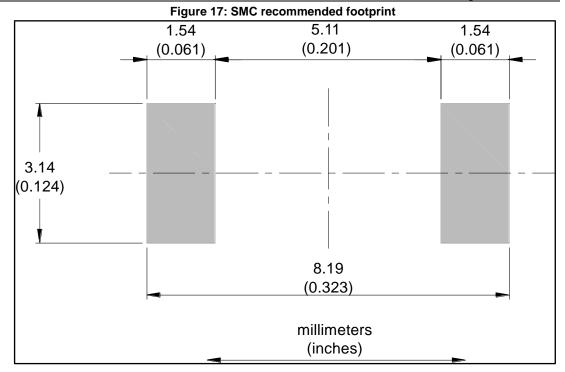


Table 7: SMC package mechanical data

	Dimensions			
Ref.	Millir	neters	Inc	hes
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.0748	0.0965
A2	0.05	0.20	0.0020	0.0079
b	2.90	3.20	0.1142	0.1260
С	0.15	0.40	0.0059	0.0157
D	5.55	6.25	0.2185	0.2461
E	7.75	8.15	0.3051	0.3209
E1	6.60	7.15	0.2598	0.2815
E2	4.40	4.70	0.1732	0.1850
L	0.75	1.50	0.0295	0.0591



Ordering information STTH212

# 3 Ordering information

**Table 8: Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STTH212U	U22	SMB	0.110 g	2500	Tape and reel
STTH212S	S12	SMC	0.243 g	2500	Tape and reel

## 4 Revision history

**Table 9: Document revision history** 

Date	Revision	Changes
28-Jun-2005	1	First issue
12-Jun-2017	2	Updated cover image. Removed DO-201AD package.

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